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XA-10097  
PATENT APPLICATION #2

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Michitaro KANAMITSU et al.

Intl. Appln. No.: PCT/JP02/01846

Intl. Filing Date: 28 February 2002

For: NONVOLATILE SEMICONDUCTOR STORAGE UNIT

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450  
Attn: Mail Stop PCT, DO/EO/US

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any  
assertion as to materiality or prior art effect, the  
documents listed on the attached Form PTO-1449 are hereby  
cited.

Documents AH-AJ on the attached List were cited in the  
International Search Report (copy attached).

Documents AO-AQ (copies herewith) are cited in the

specification, on page 2, and their relevance is indicated therein.

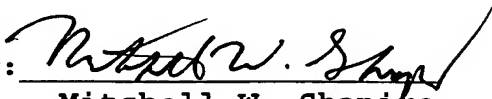
Respectfully submitted,

MWS:jab

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July 15, 2004

By:

  
Mitchell W. Shapiro  
Reg. No. 31,568

FORM PTO-1449		Atty. Docket No. XA-10097	Appln. No. 33/501391
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b>		Applicant Michitaro KANAMITSU et al.	
		Filing Date Herewith	Group

**U.S. PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

**FOREIGN PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AH	11-250681	9/17/99	Japan			No
	AI	7-307098	11/21/95	Japan			No
	AJ	10-188576	7/21/98	Japan			No
	AK						
	AL						
	AM						
	AN						

**OTHER (including author, title, date, pertinent pages, etc.)**

AO	K. Imamiya et al., "MP6.6 A 130mm <sup>2</sup> 256 Mb NAND Flash with Shallow Trench Isolation Technology", <u>1999 IEEE International Solid-State Circuits Conference</u> .
AP	K. Suh et al., "TA7.5: A 3.3V 32 Mb NAND Flash Memory with Incremental Step Pulse Programming Scheme", <u>1995 IEEE International Solid-State Circuits Conference</u> , pp. 128-129.
AQ	K. Imamiya et al., "TA7.6: A 35 ns-Cycle-Time 3.3V-Only 32 Mb NAND Flash EEPROM", <u>1995 IEEE International Solid-State Circuits Conference</u> , pp. 130-131.

Examiner	Date Considered
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.